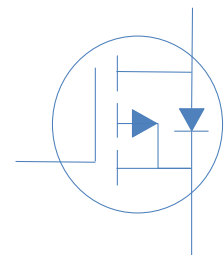
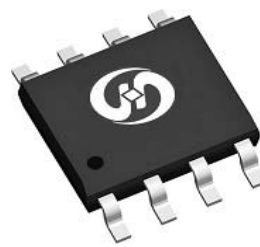


V_{DS}		-60	V
$R_{DS(on),typ}$	$V_{GS}=10V$	35	m
$R_{DS(on),typ}$	$V_{GS}=4.5V$	45	m
I_D (Silicon Limited)		-7.5	A



Part Number	Package	Marking
HTS410P06	SOIC-8	TS410P06

Absolute Maximum Ratings at T_J

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	-7.5	A
		T_C	-5	
Drain to Source Voltage	V_{DS}	-	-60	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	-30	A
		A_S	$L=0.1mH, T_C$	
	P_D	T_C	3	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	

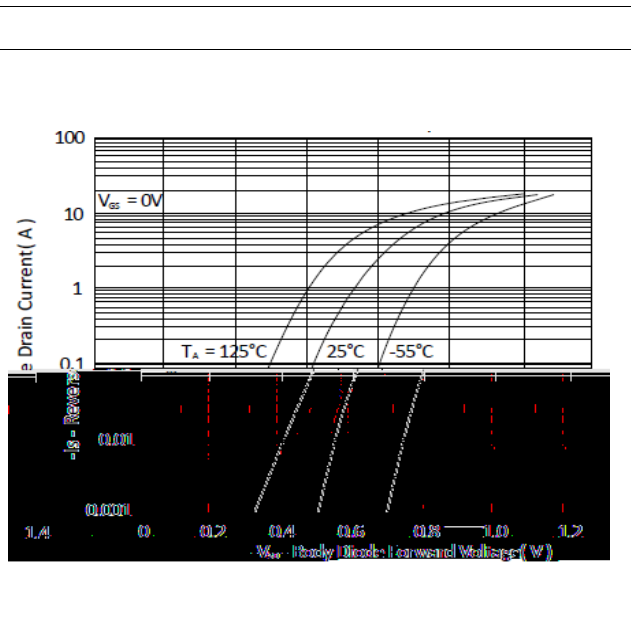
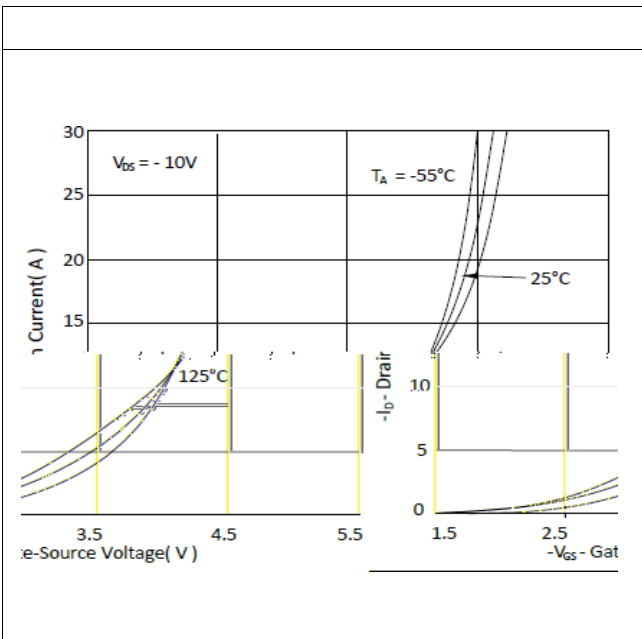
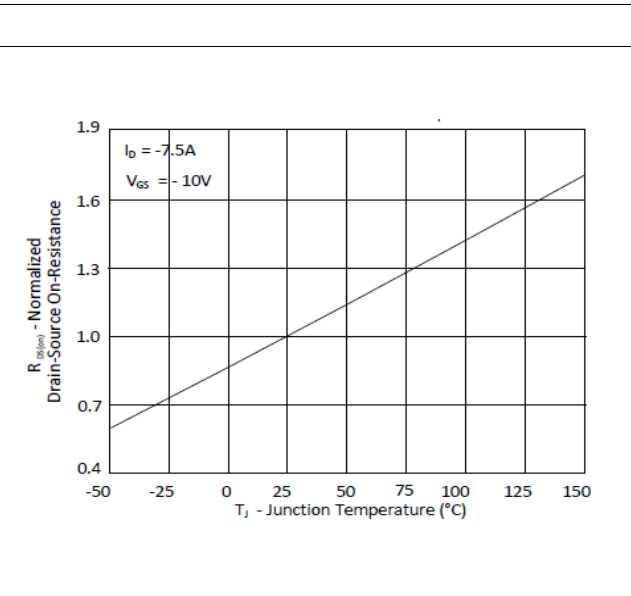
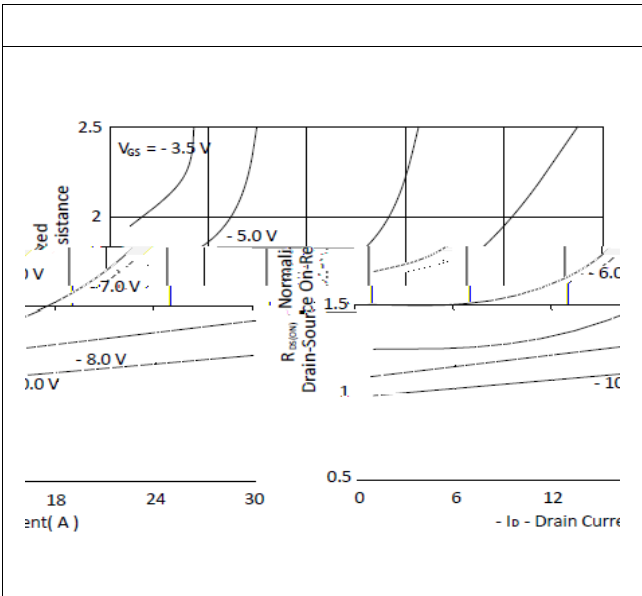
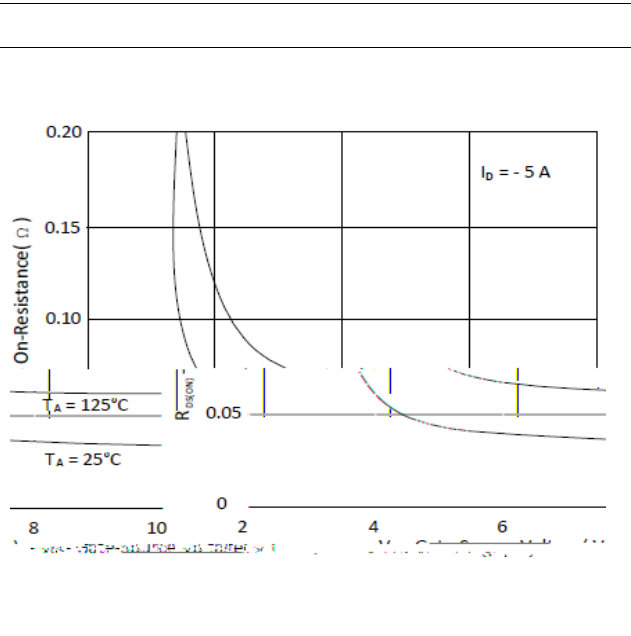
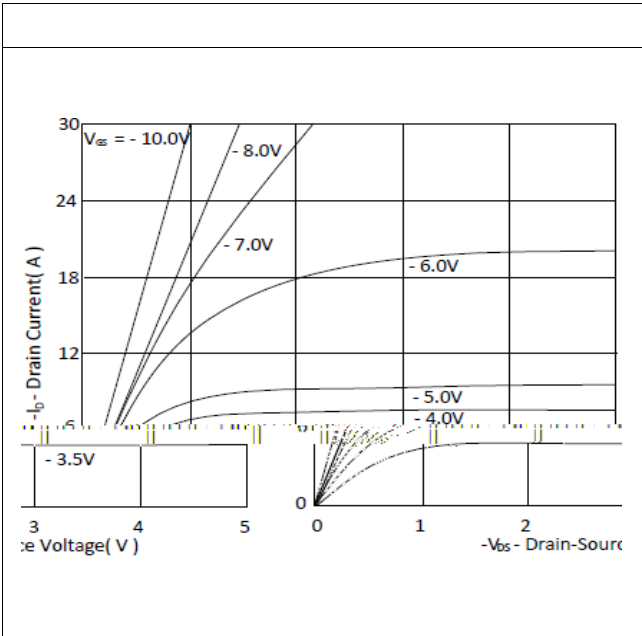
Absolute Maximum Ratings

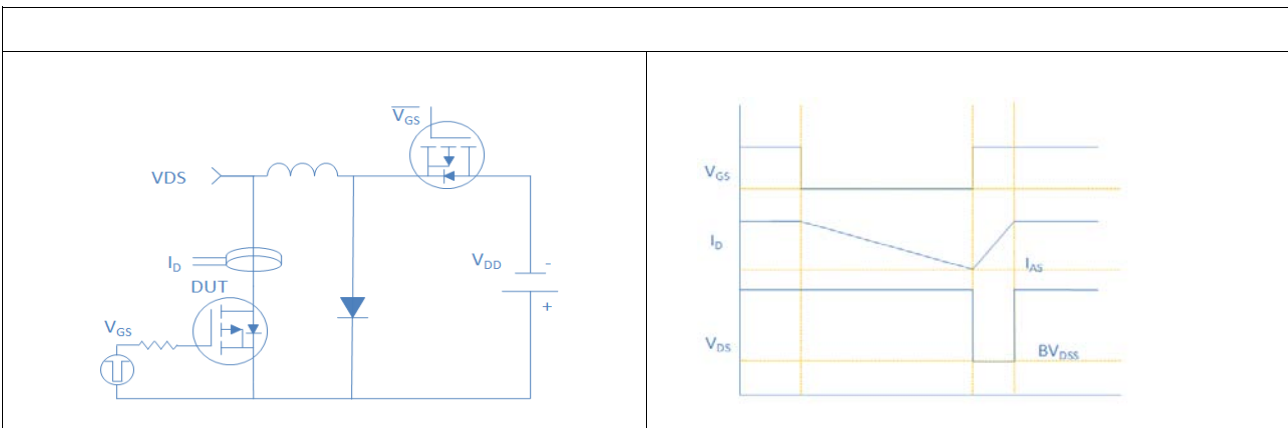
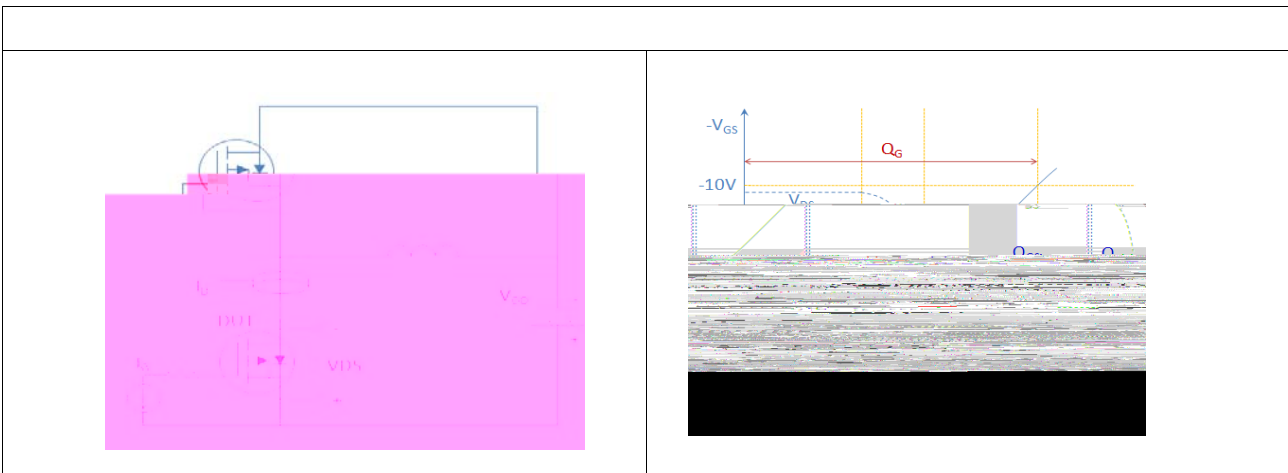
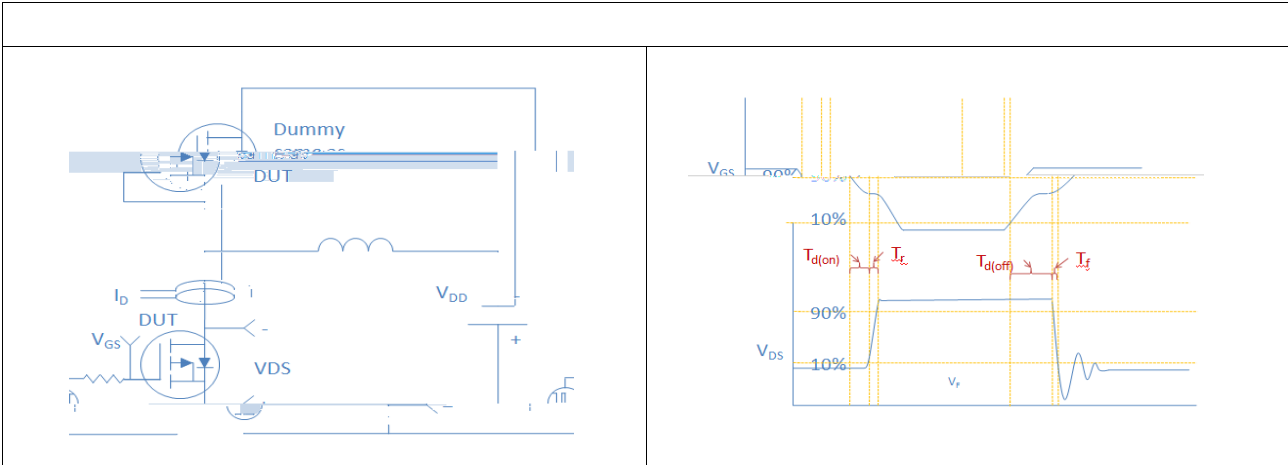
Parameter	Symbol	Max	Unit
	R_{JA}	50	
	R_{JC}	25	

	Symbol	Conditions	Value			Unit
			min	typ	max	
	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250 A$	-60	-	-	V
	V	$V_{GS}=V_{DS}, I_D=-250 A$	-1.0	-1.8	-3.0	
rain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=-48V, T_j$	-	-	-1	A
		$V_{GS}=0V, V_{DS}=-40V, T_j$	-	-	-25	
Package Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
on Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-7.5A$	-	35	40	m
		$V_{GS}=-4.5V, I_D=-5A$	-	45	55	
ce	g	$V_{DS}=-5V, I_D=-7.5A$	-	32	-	S
e	R_G	$V_{GS}=15mV, V_{DS}$	-	6.5	-	

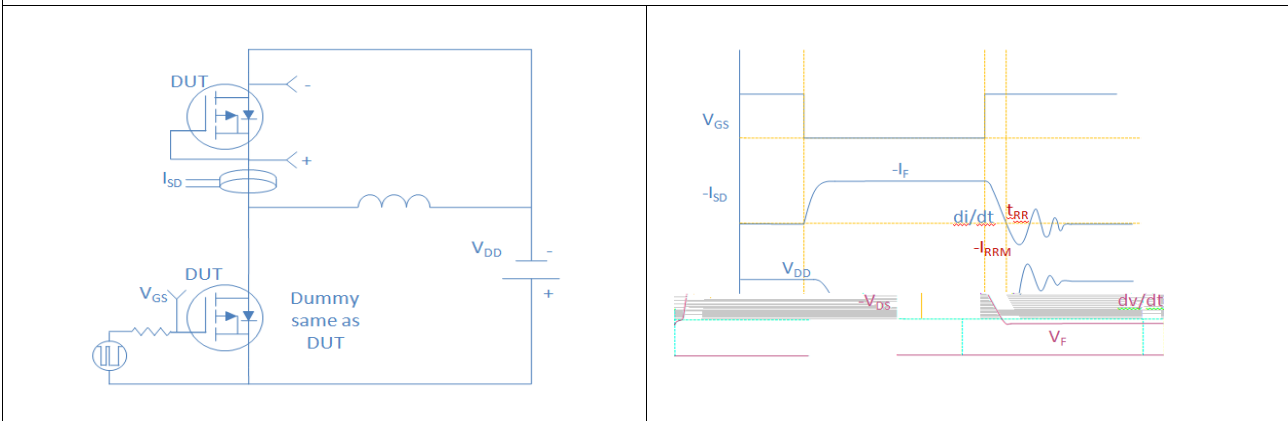
nce	C_{iss}		-	2975	-	
tance	C_{oss}	$V_{GS}=0V, V_{DS}$	-	240	-	
	C_{rss}		-	150	-	
	$Q_g(10V)$			-	45	-
	Q_{gs}	$V_{DD}=-30V, I_D=-7.5A, V_{GS}=-10V$	-	8.0	-	
	Q_{gd}		-	7.5	-	
Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-1A, V_{GS}=-10V,$ $R_G=6 \Omega$	-	12	-	ns
	t_r		-	15	-	
	t		-	40	-	
	t		-	20	-	

	V_{SD}	$V_{GS}=0V, I = -2.3A$	-		1.3	V
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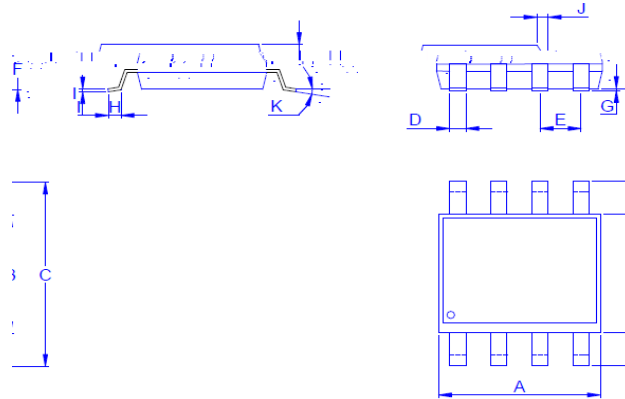


Diode Recovery Test



Package Outline

SIIC-8, 8leads



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
Min.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°